

400-1100nm High-speed Silicon-based Bias Photodetector, Active Area Φ250um, Rise Time 150ps



Product Description

IdealPhotonics' high-speed silicon-based bias photodetector has a light sensitivity range covering 400nm to 1100nm. It features extremely low noise, fast response, no gain, and low cost. It is suitable for conventional optoelectronic detection applications, offering excellent performance and high cost-effectiveness. Quan orientation technical support is provided, and it is commonly used for visible and infrared light measurement

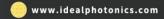
Part Number

PDSBH2P

Product features

Sensitivity range covers 400nm to 1100nm, commonly used for visible and near-infrared light measurement. Bias-type detector with extremely low noise,









fast response, and no gain. Low cost, suitable for intensity-time waveform measurements of high-speed laser pulses or light-emitting v Excellent performance, high cost-effectiveness, and comprehensive orientation technical support. Provides non-standard customization services

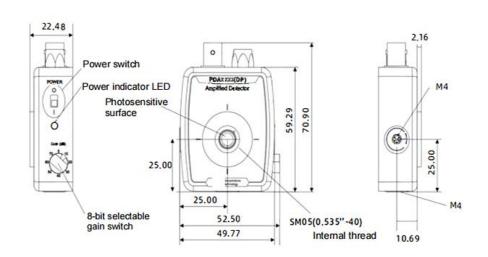
Application area

Visible and near-infrared light measurement.

Parameters

Dimensional Drawing

Dimension



Main Parameters

Main Farametere					
Parameter	Value				
Input Coupling Method	Window piece	Ball lens	FC/PC Optical Fiber Mount		
Wavelength Range	400-1100nm, Peak Wavelength 730nm				
Peak Responsivity	0.46A/W				
3dB Bandwidth (@50 Ω)	2Ghz		1GHz		



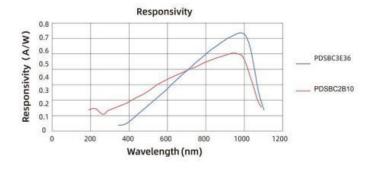






Rise/Fall Time (@50 Ω)	150ps/1	150ps	1ns/1ns		
NEP	9.29× 10-1	5W/Hz1/2	9.5 $ imes$ 10-15W/Hz1/2		
Dark Current	35p	Α	126pA		
Output Voltage	2V(M	ax)	3.3V(Max)		
Junction Capacitance	1.73pF				
Bias Voltage	12V				
Output Current	0~10mA				
Operating Impedance	50 Ω				
Active Area	Ф 250um				
Photosensitive Surface	Plane Anti-Reflection Coating	Lens Size 0.059" (1.50mm)	Embedded Coupling Lens 0.059" (1.50mm)		
Detector Net Weight	0.18kg				
Operating/Storage Temperature	0-40°C				
Appearance Dimensions	2.21" X 1.4" X 0.80" (56.1 mm X 35.6 mm X 20.3mm)				
Power Supply Battery	Signal Int	terface	SMA (DC Coupled)		
A23 ,12VDC , 40mAh	Mounting I	nterface	M4× 1		

SI Response Curve:



Attachment 1: Optional Configuration Table









Silicon-based Bias Photodetect or	Optional Configuration						
Product Name	Material	Тур	Features	Wavelength Range Sensitive Area	Bandwid th	Input Coupli ng Metho d	Optional Configurati on
PD: "Photodetect or"	S: Si Silicon-bas ed	B: Bias typ e	H: High-spe ed type	4G025: 400-1100nm Φ250um	2 : 2G Hz	W: Windo w piece	
					1 : 1G Hz	L: Ball lens	
						P: FC/PC Optical Fiber Mount	

Attachment 2: Model Number and Product Code Comparison Table

Model	Part Number	Specs
PDSBH2W	A80153424	400-1100nm High-speed Silicon-based Bias Photodetector, Active Area Φ 250um, Rise Time 150ps, Bandwidth 2GHz, Input Coupling: Window piece
PDSBH2L	A80153425	400-1100nm High-speed Silicon-based Bias Photodetector, Active Area Φ 250um, Rise Time 150ps, Bandwidth 2GHz, Input Coupling: Ball lens
PDSBH2P	A80153426	400-1100nm High-speed Silicon-based Bias Photodetector, Active Area Φ 250um, Rise Time 150ps, Bandwidth 2GHz, Input Coupling: FC/PC Optical Fiber Mount
PDSBH1P	A80153427	400-1100nm High-speed Silicon-based Bias Photodetector, Active Area Φ 250um, Rise Time 1ns, Bandwidth 1GHz, Input Coupling: FC/PC Optical Fiber Mount



